

**Method for fabricating thin film transistor**

Publication number: GB2338343

Publication date: 1999-12-15

Inventor: MOON DAE-GYU (KR)

Applicant: LG LCD INC (KR); LG PHILIPS LCD CO LTD (KR)

Classification:

- international: H01L21/20; H01L21/336; H01L21/02; (IPC1-7):  
H01L21/20

- European: H01L21/20D2; H01L21/336D2C

Application number: GB19990013338 19990608

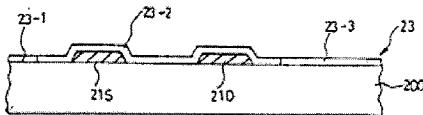
Priority number(s): KR19980021288 19980609

Also published as:

US6300175 (B1)

[Report a data error here](#)**Abstract of GB2338343**

A method of fabricating a thin film transistor comprises crystallizing an amorphous silicon layer 22 having sloping surface and flat surface by SLS technique using a laser beam having predetermined energy density so as to melt the sloping surface as well as the flat surface of the amorphous silicon layer 22 to form a crystallized silicon layer 23 and forming the active layer by selectively etching the crystallized silicon layer. The laser beam is applied non-vertically to the sloping surface while the laser beam is applied vertically to the flat surface. Although the sloping surface and the flat surface of the amorphous silicon layer 22 are irradiated with laser beam having same laser energy density, the absorbed energy density of the sloping surface may be lower than that of the flat surface. The laser beam requires first energy density to substantially melt the sloping surface and second energy density to substantially melt the flat surface of the amorphous silicon 22. The amorphous silicon layer 22 is irradiated with the laser beam having the first energy density to substantially melt both the sloping and flat surfaces.

**FIG.28**Data supplied from the **esp@cenet** database - Worldwide